



No.3461A

2SK1458

N-Channel Silicon MOSFET

Ultarahigh-Speed Switching Applications

Features

- Low ON-state resistance.
 - Ultrahigh-speed switching.
 - Micaless package facilitating mounting.

Absolute Maximum Ratings at Ta = 25°C

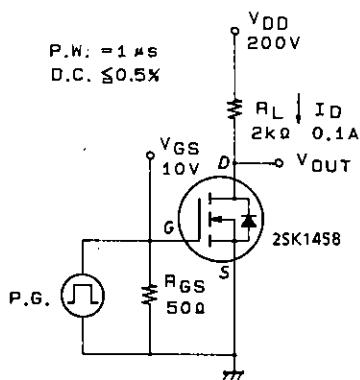
Absolute Maximum Ratings at $T_A = 25^\circ\text{C}$		unit
Drain-to-Source Voltage	V_{DSS}	900 V
Gate-to-Source Voltage	V_{GSS}	± 30 V
Drain Current(DC)	I_D	0.2 A
Drain Current(Pulse)	I_{DP}	PW $\leq 10\mu\text{s}$, duty cycle $\leq 1\%$ 0.4 A
Allowable Power Dissipation	P_D	2.0 W
		T _c = 25°C 20 W
Channel Temperature	T _{ch}	150 °C
Storage Temperature	T _{stg}	-55 to +150 °C

Electrical Characteristics at Ta = 25°C

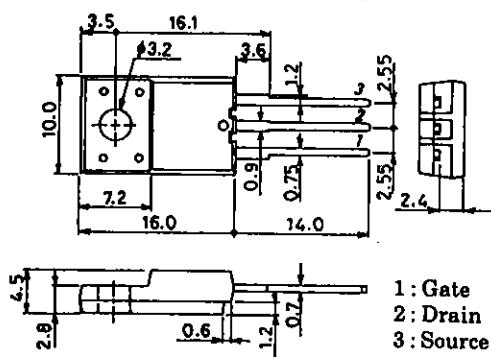
Electrical Characteristics at $T_A = 25^\circ C$		$I_D = 1\text{mA}, V_{GS} = 0$	min	typ	max	unit
D-S Breakdown Voltage	$V_{(BR)DSS}$		900			V
Zero-Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 900V, V_{GS} = 0$			1.0	mA
Gate-to-Source Leakage Current	I_{GSS}	$V_{GS} = \pm 30V, V_{DS} = 0$			± 100	nA
Cutoff Voltage	$V_{GS(\text{off})}$	$V_{DS} = 10V, I_D = 1\text{mA}$	2.0		3.0	V
Forward Transfer Admittance	$ Y_{fs} $	$V_{DS} = 20V, I_D = 0.1A$	0.08	0.15		S
Static Drain-to-Source	$R_{DS(on)}$	$I_D = 0.1A, V_{GS} = 10V$		50	70	Ω
ON-State Resistance						
Input Capacitance	C_{iss}	$V_{DS} = 20V, f = 1\text{MHz}$	45			pF
Output Capacitance	C_{oss}	$V_{DS} = 20V, f = 1\text{MHz}$	25			pF
Reverse Transfer Capacitance	C_{rss}	$V_{DS} = 20V, f = 1\text{MHz}$	10			pF
Turn-ON Delay Time	$t_{d(on)}$		10			ns
Rise Time	t_r	$I_D = 0.1A, V_{GS} = 10V$	15			ns
Turn-OFF Delay Time	$t_{d(off)}$	$V_{DD} = 200V, R_{GS} = 50\Omega$	30			ns
Fall Time	t_f		180			ns
Diode Forward Voltage	V_{SD}	$I_S = 0.2A, V_{GS} = 0$			1.8	V

(Note) Be careful in handling the 2SK1458 because it has no protection diode between gate and source.

Switching Time Test Circuit

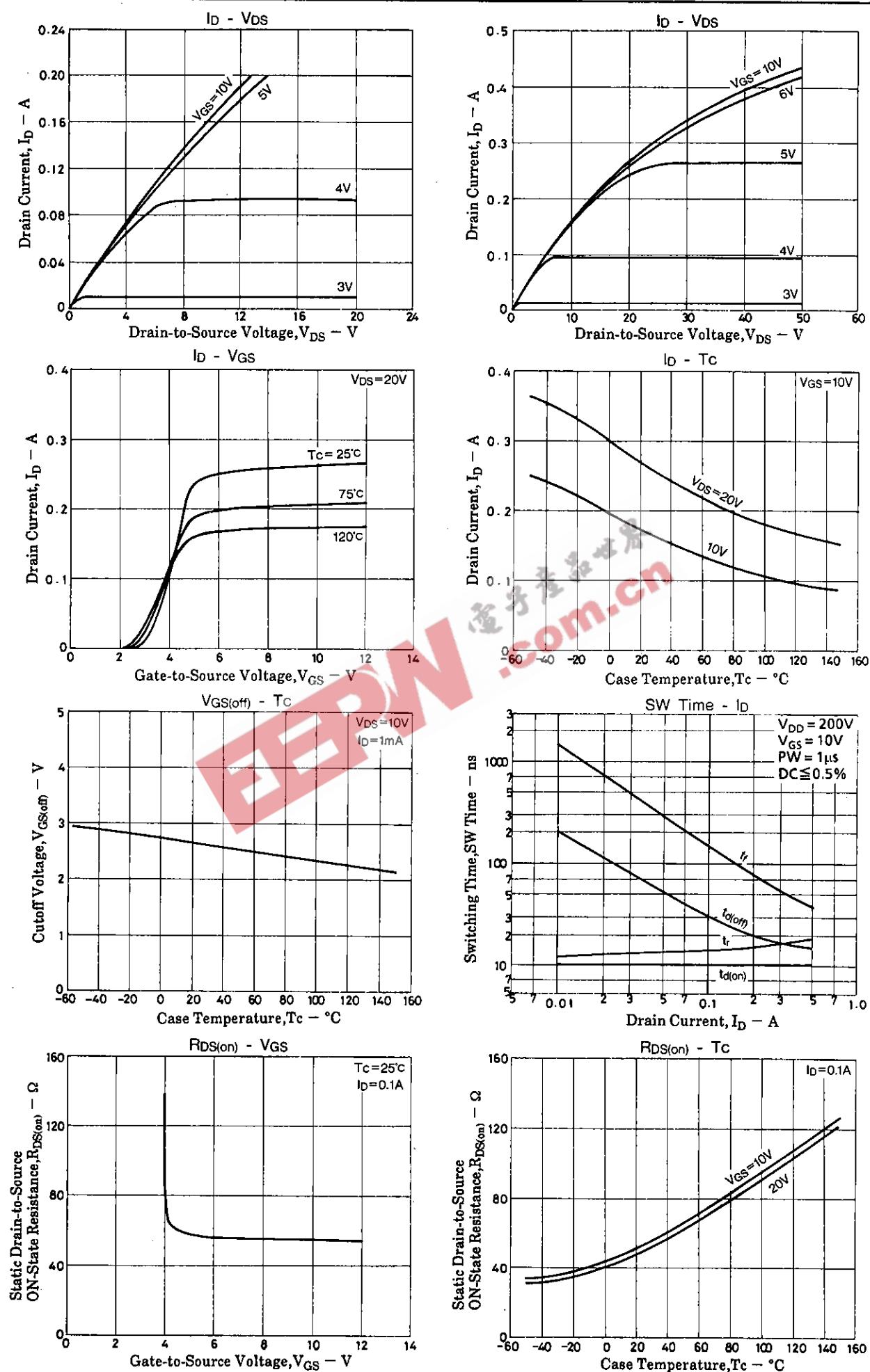


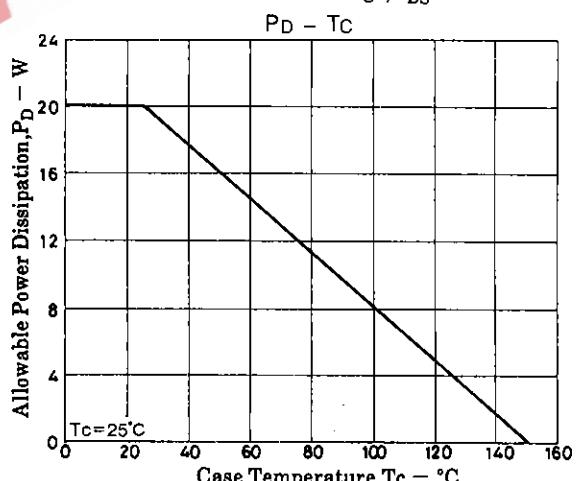
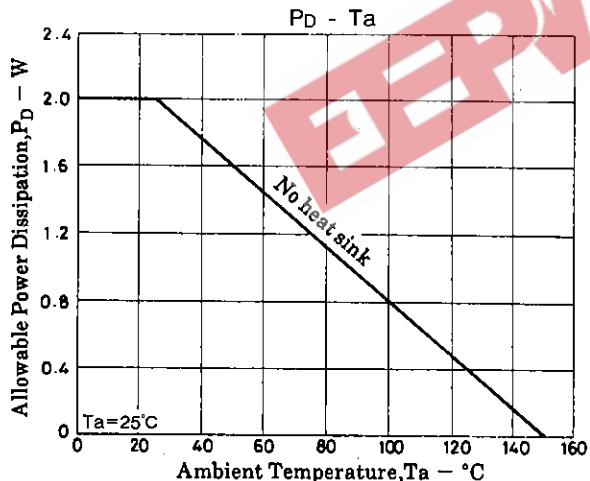
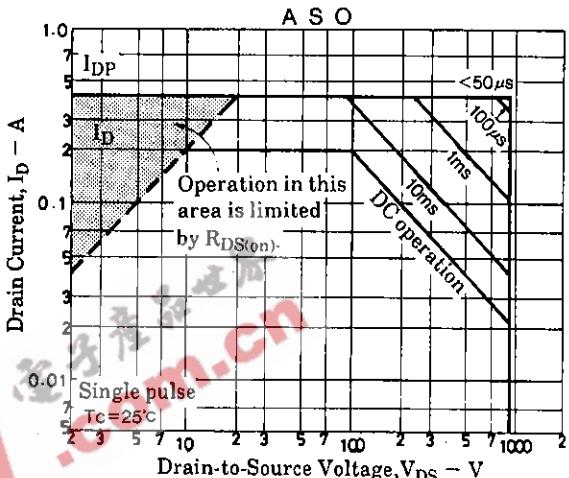
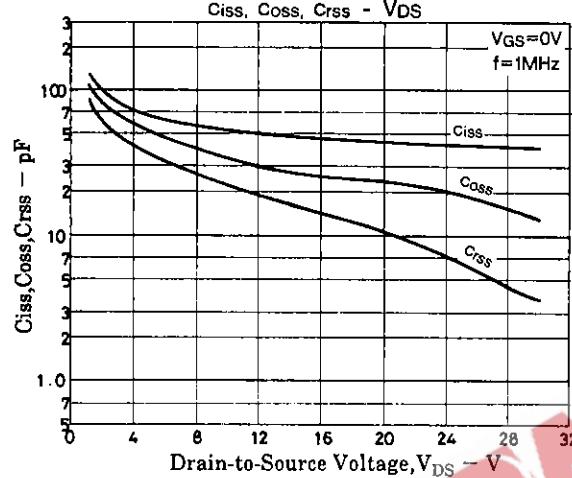
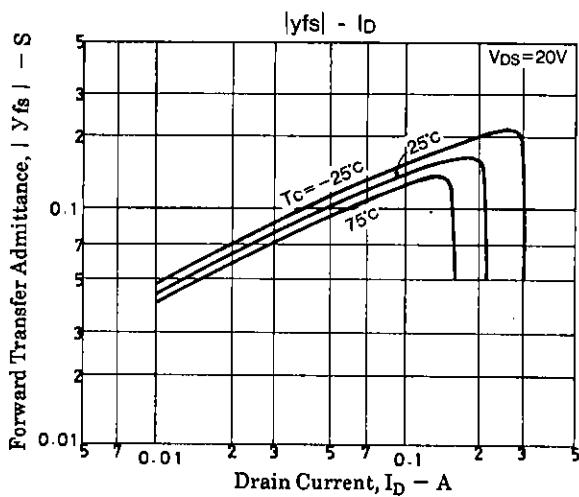
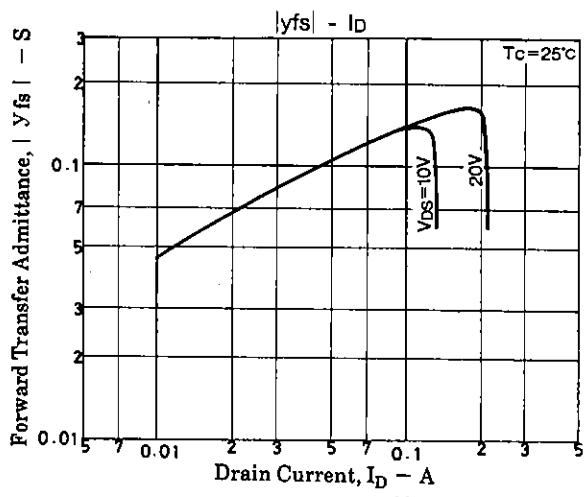
Package Dimensions 2078B (unit : mm)



SANYO : TO-220FI(LS)

SANYO Electric Co.,Ltd. Semiconductor Business Headquarters
TOKYO OFFICE Tokyo Bldg., 1-10, 1 Chome, Ueno, Taito-ku, TOKYO, 110 JAPAN





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